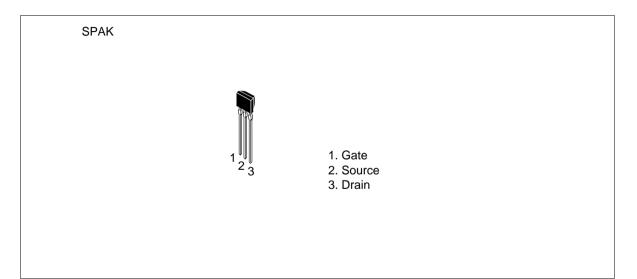
## Silicon N-Channel Junction FET

# HITACHI

#### Application

VHF amplifier, Mixer, local oscillator

#### Outline



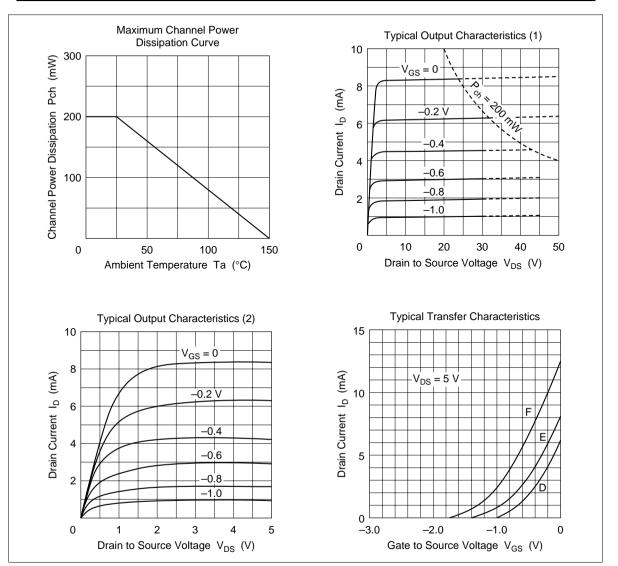


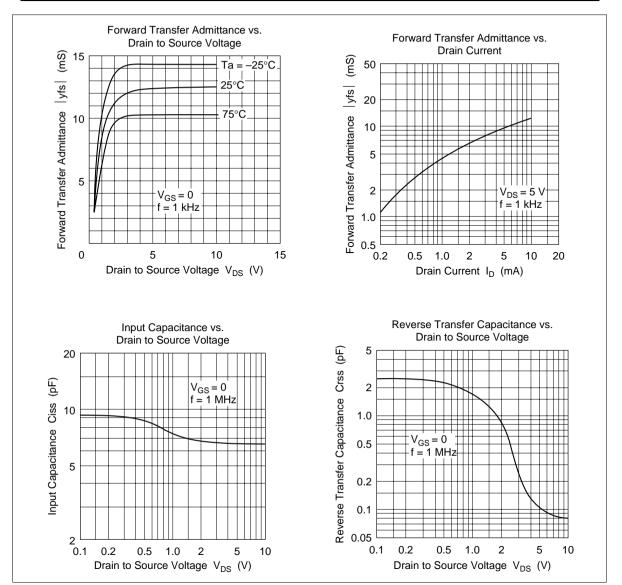
## **Absolute Maximum Ratings** (Ta = $25^{\circ}$ C)

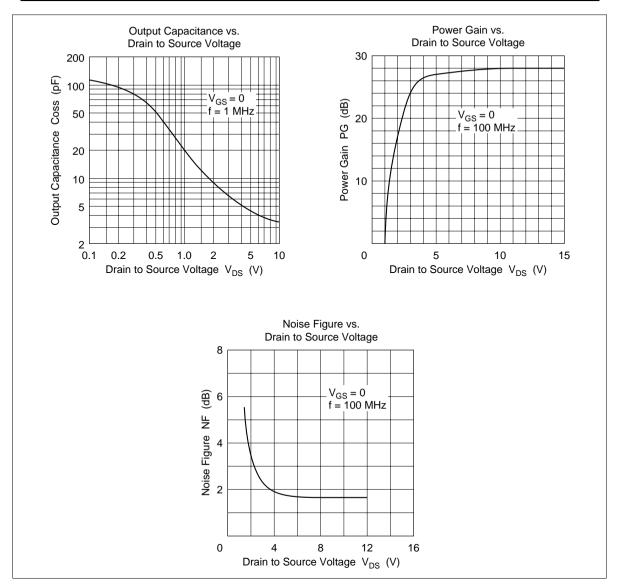
Item	Symbol	Ratings	Unit	
Gate to drain voltage	$V_{GDO}$	-30	V	
Gate current	Ι <sub>G</sub>	10	mA	
Drain current	Ι <sub>D</sub>	20	mA	
Channel power dissipation	Pch	200	mW	
Channel temperature	Tch	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

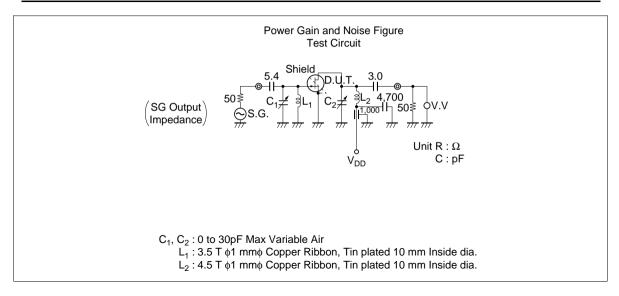
## **Electrical Characteristics** (Ta = 25°C)

Item	Symbol	Min	Тур	Max	Unit	Test conditions	
Gate to drain breakdown voltage	$V_{(\text{BR})\text{GDO}}$	-30	_	_	V	$I_{g} = -100 \ \mu A, \ I_{g} = 0$	
Gate cutoff current	I <sub>GSS</sub>	_	—	-10	nA	$V_{GS} = -0.5 \text{ V}, V_{DS} = 0$	
Drain current	I <sub>DSS</sub> *1	4	—	20	mA	$V_{DS} = 5 V, V_{GS} = 0$	
Gate to source cutoff voltage	$V_{GS(off)}$	—	—	-3	V	$V_{\rm DS} = 5 \text{ V}, \text{ I}_{\rm D} = 10 \mu\text{A}$	
Forward transfer admittance	y <sub>fs</sub>	8	10	_	mS	$V_{DS} = 5 \text{ V}, V_{GS} = 0, f = 1 \text{ kHz}$	
Input capacitance	Ciss	—	6.8		pF	$V_{DS} = 5 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	
Reverse transfer capacitance	Crss	_	0.1		pF	_	
Power gain	PG	20	27	—	dB	$V_{DS} = 5 V, V_{GS} = 0,$ f = 100 MHz	
Noise figure	NF	_	1.7	2.5	dB	_	
Note: 1. The 2SK522 is grouped by I <sub>DSS</sub> as follows.							
Drain D E		F					
I <sub>DSS</sub> 4 to 8 6	to 10	10 to 2	0				

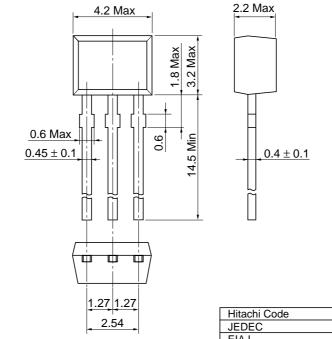








Unit: mm



Hitachi Code	SPAK
JEDEC	_
EIAJ	—
Weight (reference value)	0.10 g

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